

IN THE CLAIMS

1-3. (Canceled).

4. (Previously Presented) The semiconductor device of claim 8, wherein said p-type layers and said n-type layers are made of at least one selected from polysilicon, amorphous silicon, single-crystal silicon on a insulating layer, SiC and SiGe.

5. (Previously Presented) The semiconductor device of claim 8, wherein said p-type layers and said n-type layers are formed so as to have the same width and the same concentration of impurities, in the same conductivity type, respectively.

6. (Currently Amended) The semiconductor device of claim 8, wherein a diffusion region having a ~~different~~ conductivity type different from ~~that of~~ said semiconductor layer first conductivity type is formed on the closest side to said protective diode of said transistor cells ~~arranged~~, said diffusion region having no other diffusion region therein, and said source wiring contacted to the most inner layer of said protective diode is contacted to said diffusion region.

7. (Canceled).

8. (Currently Amended) A semiconductor device comprising:
an insulating gate field effect transistor comprising a plurality of transistor cells ~~which are~~ connected in parallel and arranged in a semiconductor layer ~~and connected in parallel~~ of a first conductivity type ; and

a protective diode connected between a gate and a source of said insulating gate field effect transistor to prevent breakdown due to a voltage greater than or equal to a particular value,

wherein said protective diode is formed as a bidirectional diode in which one or more closed ring-shaped p-type layers and one or more closed ring-shaped n-type layers are flatly and alternately provided on an insulating layer at a peripheral portion of a region of said transistor cells, a source wiring contacts with the most inner layer of said protective diode, and a closed ring-shaped metal film contacts with the most outer layer of said protective diode, said closed ring-shaped metal film being successively formed with a gate electrode pad comprising a metal film;

wherein said ring-shaped metal film substantially contacts the full circumferential length of the most outer layer; and

wherein said ring-shaped metal film is a gate wiring which has gate connecting portions so as to connect to gate electrodes of said transistor cells with partial striding over said protective diode, and said gate connecting portions and source connecting portions of said source wiring which are contacted with said most inner layer are alternately formed in plan view.

9. (Canceled).

10. (New) A semiconductor device comprising:

an insulating gate field effect transistor comprising a plurality of transistor cells arranged in a semiconductor layer and connected in parallel;

a protective diode connected between a gate and a source of said insulating gate field effect transistor to prevent breakdown due to a voltage greater than or equal to a particular value, said protective diode formed as a bidirectional diode having at least one closed ring-shaped p-type layer, flatly and alternately provided with at least one closed ring-shaped n-type layer, on an insulating layer at a peripheral portion of a region of said transistor cells,

a source wiring in contact with the most inner layer of said protective diode, and
a gate wiring of a closed ring-shaped metal film substantially contacting the full circumferential length of the outermost layer of said protective diode;

wherein said closed ring-shaped metal film is connected to a gate electrode pad comprising a metal film provided within said protective diode formed by said closed ring-shaped p-type and n-type layers, with partial striding over said protective diode.